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#### Understanding <u>Embedded - FPGAs (Field</u> <u>Programmable Gate Array)</u>

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

#### **Applications of Embedded - FPGAs**

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

#### Details

Product Status	Obsolete
Number of LABs/CLBs	-
Number of Logic Elements/Cells	-
Total RAM Bits	147456
Number of I/O	154
Number of Gates	1000000
Voltage - Supply	1.14V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	208-BFQFP
Supplier Device Package	208-PQFP (28x28)
Purchase URL	https://www.e-xfl.com/product-detail/microsemi/m1a3p1000l-1pq208

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong



Flash\*Freeze Technology and Low Power Modes

- Avoid using pull-ups and pull-downs on I/Os because these resistors draw some current. Avoid driving resistive loads or bipolar transistors, since these draw a continuous current, thereby adding to the static current.
- When partitioning the design across multiple devices, minimize I/O usage among the devices.

## Conclusion

Microsemi IGLOO, IGLOO nano, IGLOO PLUS, ProASIC3L, and RT ProASIC3 family architectures are designed to achieve ultra-low power consumption based on enhanced nonvolatile and live-at-power-up flash-based technology. Power consumption can be reduced further by using Flash\*Freeze, Static (Idle), Sleep, and Shutdown power modes. All these features result in a low power, cost-effective, single-chip solution designed specifically for power-sensitive and battery-operated electronics applications.

# **Related Documents**

## **Application Notes**

Embedded SRAM Initialization Using External Serial EEPROM http://www.microsemi.com/soc/documents/EmbeddedSRAMInit\_AN.pdf

# **List of Changes**

The following table lists critical changes that were made in each version of the chapter.

Date	Changes	Page	
July 2010	This chapter is no longer published separately with its own part number and version but is now part of several FPGA fabric user's guides.	N/A	
v2.3 (November 2009)	The "Sleep Mode" section was revised to state the VJTAG and VPUMP, as well as VCC, are grounded during Sleep mode (SAR 22517).		
	Figure 2-6 • Controlling Power-On/-Off State Using Microprocessor and Power FET and Figure 2-7 • Controlling Power-On/-Off State Using Microprocessor and Voltage Regulator were revised to show that VJTAG and VPUMP are powered off during Sleep mode.	33	
v2.2 (December 2008)	IGLOO nano devices were added as a supported family.	N/A	
	The "Prototyping for IGLOO and ProASIC3L Devices Using ProASIC3" section was removed, as these devices are now in production.	N/A	
	The "Additional Power Conservation Techniques" section was revised to add RT ProASIC3 devices.	41	
v2.0 (October 2008)	The "Flash*Freeze Management FSM" section was updated with the following information: The FSM also asserts Flash_Freeze_Enabled whenever the device enters Flash*Freeze mode. This occurs after all housekeeping and clock gating functions have completed.	37	

## **VersaNet Global Network Distribution**

One of the architectural benefits of low power flash architecture is the set of powerful, low-delay VersaNet global networks that can access the VersaTiles, SRAM, and I/O tiles of the device. Each device offers a chip global network with six global lines (except for nano 10 k, 15 k, and 20 k gate devices) that are distributed from the center of the FPGA array. In addition, each device (except the 10 k through 30 k gate device) has four quadrant global networks, each consisting of three quadrant global net resources. These quadrant global networks can only drive a signal inside their own quadrant. Each VersaTile has access to nine global line resources—three quadrant and six chip-wide (main) global networks—and a total of 18 globals are available on the device (3 × 4 regional from each quadrant and 6 global).

Figure 3-1 shows an overview of the VersaNet global network and device architecture for devices 60 k and above. Figure 3-2 and Figure 3-3 on page 50 show simplified VersaNet global networks.

The VersaNet global networks are segmented and consist of spines, global ribs, and global multiplexers (MUXes), as shown in Figure 3-1. The global networks are driven from the global rib at the center of the die or quadrant global networks at the north or south side of the die. The global network uses the MUX trees to access the spine, and the spine uses the clock ribs to access the VersaTile. Access is available to the chip or quadrant global networks and the spines through the global MUXes. Access to the spine using the global MUXes is explained in the "Spine Architecture" section on page 57.

These VersaNet global networks offer fast, low-skew routing resources for high-fanout nets, including clock signals. In addition, these highly segmented global networks offer users the flexibility to create low-skew local clock networks using spines for up to 252 internal/external clocks or other high-fanout nets in low power flash devices. Optimal usage of these low-skew networks can result in significant improvement in design performance.





Figure 3-1 • Overview of VersaNet Global Network and Device Architecture

# Chip and Quadrant Global I/Os

The following sections give an overview of naming conventions and other related I/O information.

## Naming of Global I/Os

In low power flash devices, the global I/Os have access to certain clock conditioning circuitry and have direct access to the global network. Additionally, the global I/Os can be used as regular I/Os, since they have identical capabilities to those of regular I/Os. Due to the comprehensive and flexible nature of the I/Os in low power flash devices, a naming scheme is used to show the details of the I/O. The global I/O uses the generic name Gmn/IOuxwByVz. Note that Gmn refers to a global input pin and IOuxwByVz refers to a regular I/O Pin, as these I/Os can be used as either global or regular I/Os. Refer to the I/O Structures chapter of the user's guide for the device that you are using for more information on this naming convention.

Figure 3-4 represents the global input pins connection. It shows all 54 global pins available to access the 18 global networks in ProASIC3E families.



Figure 3-4 • Global Connections Details

Clock Conditioning Circuits in Low Power Flash Devices and Mixed Signal FPGAs







GAA[0:2]: GA represents global in the northwest corner of the device. A[0:2]: designates specific A clock source.

Notes:

- Represents the global input pins. Globals have direct access to the clock conditioning block and are not routed via the FPGA fabric. Refer to the "User I/O Naming Conventions in I/O Structures" chapter of the appropriate device user's guide.
- 2. Instantiate the routed clock source input as follows:
  - a) Connect the output of a logic element to the clock input of a PLL, CLKDLY, or CLKINT macro.
  - b) Do not place a clock source I/O (INBUF or INBUF\_LVPECL/LVDS/B-LVDS/M-LVDS/DDR) in a relevant global pin location.
- 3. IGLOO nano and ProASIC3 nano devices do not support differential inputs.

Figure 4-8 • Clock Input Sources Including CLKBUF, CLKBUF\_LVDS/LVPECL, and CLKINT (60 k gates devices and above)

Clock Conditioning Circuits in Low Power Flash Devices and Mixed Signal FPGAs

Each group of control bits is assigned a specific location in the configuration shift register. For a list of the 81 configuration bits (C[80:0]) in the CCC and a description of each, refer to "PLL Configuration Bits Description" on page 106. The configuration register can be serially loaded with the new configuration data and programmed into the CCC using the following ports:

- SDIN: The configuration bits are serially loaded into a shift register through this port. The LSB of the configuration data bits should be loaded first.
- SDOUT: The shift register contents can be shifted out (LSB first) through this port using the shift operation.
- SCLK: This port should be driven by the shift clock.
- SSHIFT: The active-high shift enable signal should drive this port. The configuration data will be shifted into the shift register if this signal is HIGH. Once SSHIFT goes LOW, the data shifting will be halted.
- SUPDATE: The SUPDATE signal is used to configure the CCC with the new configuration bits when shifting is complete.

To access the configuration ports of the shift register (SDIN, SDOUT, SSHIFT, etc.), the user should instantiate the CCC macro in his design with appropriate ports. Microsemi recommends that users choose SmartGen to generate the CCC macros with the required ports for dynamic reconfiguration.

Users must familiarize themselves with the architecture of the CCC core and its input, output, and configuration ports to implement the desired delay and output frequency in the CCC structure. Figure 4-22 shows a model of the CCC with configurable blocks and switches.

Table 4-9 to Table 4-15 on page 110 provide descriptions of the configuration data for the configuration bits.

#### Table 4-9 • Input Clock Divider, FINDIV[6:0] (/n)

FINDIV<6:0> State	Divisor	New Frequency Factor
0	1	1.00000
1	2	0.50000
:	÷	÷
127	128	0.0078125

#### Table 4-10 • Feedback Clock Divider, FBDIV[6:0] (/m)

FBDIV<6:0> State	Divisor	New Frequency Factor
0	1	1
1	2	2
:	:	÷
127	128	128

Table 4-11 • Output Frequency DividersA Output Divider, OADIV <4:0> (/u);B Output Divider, OBDIV <4:0> (/v);C Output Divider, OCDIV <4:0> (/w)

OADIV<4:0>; OBDIV<4:0>; CDIV<4:0> State	Divisor	New Frequency Factor
0	1	1.00000
1	2	0.50000
:	:	:
31	32	0.03125

#### Table 4-12 • MUXA, MUXB, MUXC

OAMUX<2:0>; OBMUX<2:0>; OCMUX<2:0> State	MUX Input Selected
0	None. Six-input MUX and PLL are bypassed. Clock passes only through global MUX and goes directly into HC ribs.
1	Not available
2	PLL feedback delay line output
3	Not used
4	PLL VCO 0° phase shift
5	PLL VCO 270° phase shift
6	PLL VCO 180° phase shift
7	PLL VCO 90° phase shift

OADIVHALF / OBDIVHALF / OCDIVHALF	OADIV<4:0> / OBDIV<4:0> / OCDIV<4:0> (in decimal)	Divider Factor	Input Clock Frequency	Output Clock Frequency (MHz)
1	2	1.5	100 MHz RC	66.7
	4	2.5	Oscillator	40.0
	6	3.5	1	28.6
	8	4.5		22.2
	10	5.5		18.2
	12	6.5		15.4
	14	7.5		13.3
	16	8.5		11.8
	18	9.5		10.5
	20	10.5		9.5
	22	11.5		8.7
	24	12.5		8.0
	26	13.5		7.4
	28	14.5		6.9
0	0–31	1–32	Other Clock Sources	Depends on other divider settings

#### Table 4-18 • Fusion Dynamic CCC Division by Half Configuration

#### Table 4-19 • Configuration Bit <76:75> / VCOSEL<2:1> Selection for All Families

	VCOSEL[2:1]								
	C	00		01		10		11	
Voltage	Min. (MHz)	Max. (MHz)	Min. (MHz)	Max. (MHz)	Min. (MHz)	Max. (MHz)	Min. (MHz)	Max. (MHz)	
IGLOO and IGLOO	PLUS								
1.2 V ± 5%	24	35	30	70	60	140	135	160	
1.5 V ± 5%	24	43.75	30	87.5	60	175	135	250	
ProASIC3L, RT Pro	ProASIC3L, RT ProASIC3, and Military ProASIC3/L								
1.2 V ± 5%	24	35	30	70	60	140	135	250	
1.5 V ± 5%	24	43.75	30	70	60	175	135	350	
ProASIC3 and Fusion									
1.5 V ± 5%	24	43.75	33.75	87.5	67.5	175	135	350	

### Table 4-20 • Configuration Bit <74> / VCOSEL<0> Selection for All Families

VCOSEL[0]	Description
0	Fast PLL lock acquisition time with high tracking jitter. Refer to the corresponding datasheet for specific value and definition.
1	Slow PLL lock acquisition time with low tracking jitter. Refer to the corresponding datasheet for specific value and definition.

## Feedback Configuration

The PLL provides both internal and external feedback delays. Depending on the configuration, various combinations of feedback delays can be achieved.

#### Internal Feedback Configuration

This configuration essentially sets the feedback multiplexer to route the VCO output of the PLL core as the input to the feedback of the PLL. The feedback signal can be processed with the fixed system and the adjustable feedback delay, as shown in Figure 4-24. The dividers are automatically configured by SmartGen based on the user input.

Indicated below is the System Delay pull-down menu. The System Delay can be bypassed by setting it to 0. When set, it adds a 2 ns delay to the feedback path (which results in delay advancement of the output clock by 2 ns).

#### Figure 4-24 • Internal Feedback with Selectable System Delay

Figure 4-25 shows the controllable Feedback Delay. If set properly in conjunction with the fixed System Delay, the total output delay can be advanced significantly.

Figure 4-25 • Internal Feedback with Selectable Feedback Delay



FlashROM in Microsemi's Low Power Flash Devices

# **Programming and Accessing FlashROM**

The FlashROM content can only be programmed via JTAG, but it can be read back selectively through the JTAG programming interface, the UJTAG interface, or via direct FPGA core addressing. The pages of the FlashROM can be made secure to prevent read-back via JTAG. In that case, read-back on these secured pages is only possible by the FPGA core fabric or via UJTAG.

A 7-bit address from the FPGA core defines which of the eight pages (three MSBs) is being read, and which of the 16 bytes within the selected page (four LSBs) are being read. The FlashROM content can be read on a random basis; the access time is 10 ns for a device supporting commercial specifications. The FPGA core will be powered down during writing of the FlashROM content. FPGA power-down during FlashROM programming is managed on-chip, and FPGA core functionality is not available during programming of the FlashROM. Table 5-2 summarizes various FlashROM access scenarios.

Access Mode	FlashROM Read	FlashROM Write
JTAG	Yes	Yes
UJTAG	Yes	No
FPGA core	Yes	No

Table 5-2 •	FlashROM	<b>Read/Write</b>	Capabilities	by	Access	Mode

Figure 5-6 shows the accessing of the FlashROM using the UJTAG macro. This is similar to FPGA core access, where the 7-bit address defines which of the eight pages (three MSBs) is being read and which of the 16 bytes within the selected page (four LSBs) are being read. Refer to the "UJTAG Applications in Microsemi's Low Power Flash Devices" section on page 363 for details on using the UJTAG macro to read the FlashROM.

Figure 5-7 on page 139 and Figure 5-8 on page 139 show the FlashROM access from the JTAG port. The FlashROM content can be read on a random basis. The three-bit address defines which page is being read or updated.



Figure 5-6 • Block Diagram of Using UJTAG to Read FlashROM Contents



FlashROM in Microsemi's Low Power Flash Devices

Figure 5-12 shows the programming file generator, which enables different STAPL file generation methods. When you select **Program FlashROM** and choose the UFC file, the FlashROM Settings window appears, as shown in Figure 5-13. In this window, you can select the FlashROM page you want to program and the data value for the configured regions. This enables you to use a different page for different programming files.

*Figure 5-12* • Programming File Generator

### Figure 5-13 • Setting FlashROM during Programming File Generation

The programming hardware and software can load the FlashROM with the appropriate STAPL file. Programming software handles the single STAPL file that contains multiple FlashROM contents for multiple devices, and programs the FlashROM in sequential order (e.g., for device serialization). This feature is supported in the programming software. After programming with the STAPL file, you can run DEVICE\_INFO to check the FlashROM content.

### Solution 4

The board-level design must ensure that the reflected waveform at the pad does not exceed the voltage overshoot/undershoot limits provided in the datasheet. This is a requirement to ensure long-term reliability.



Figure 7-12 • Solution 4

## Selectable Skew between Output Buffer Enable and Disable Times

Low power flash devices have a configurable skew block in the output buffer circuitry that can be enabled to delay output buffer assertion without affecting deassertion time. Since this skew block is only available for the OE signal, the feature can be used in tristate and bidirectional buffers. A typical 1.2 ns delay is added to the OE signal to prevent potential bus contention. Refer to the appropriate family datasheet for detailed timing diagrams and descriptions.

The skew feature is available for all I/O standards.

This feature can be implemented by using a PDC command (Table 7-5 on page 179) or by selecting a check box in the I/O Attribute Editor in Designer. The check box is cleared by default.

The configurable skew block is used to delay output buffer assertion (enable) without affecting deassertion (disable) time.



Figure 7-13 • Block Diagram of Output Enable Path





I/O Structures in IGLOO and ProASIC3 Devices

# **Board-Level Considerations**

Low power flash devices have robust I/O features that can help in reducing board-level components. The devices offer single-chip solutions, which makes the board layout simpler and more immune to signal integrity issues. Although, in many cases, these devices resolve board-level issues, special attention should always be given to overall signal integrity. This section covers important board-level considerations to facilitate optimum device performance.

## Termination

Proper termination of all signals is essential for good signal quality. Nonterminated signals, especially clock signals, can cause malfunctioning of the device.

For general termination guidelines, refer to the *Board-Level Considerations* application note for Microsemi FPGAs. Also refer to the "Pin Descriptions" chapter of the appropriate datasheet for termination requirements for specific pins.

Low power flash I/Os are equipped with on-chip pull-up/-down resistors. The user can enable these resistors by instantiating them either in the top level of the design (refer to the *IGLOO, Fusion, and ProASIC3 Macro Library Guide* for the available I/O macros with pull-up/-down) or in the I/O Attribute Editor in Designer if generic input or output buffers are instantiated in the top level. Unused I/O pins are configured as inputs with pull-up resistors.

As mentioned earlier, low power flash devices have multiple programmable drive strengths, and the user can eliminate unwanted overshoot and undershoot by adjusting the drive strengths.

## **Power-Up Behavior**

Low power flash devices are power-up/-down friendly; i.e., no particular sequencing is required for power-up and power-down. This eliminates extra board components for power-up sequencing, such as a power-up sequencer.

During power-up, all I/Os are tristated, irrespective of I/O macro type (input buffers, output buffers, I/O buffers with weak pull-ups or weak pull-downs, etc.). Once I/Os become activated, they are set to the user-selected I/O macros. Refer to the "Power-Up/-Down Behavior of Low Power Flash Devices" section on page 373 for details.

## **Drive Strength**

Low power flash devices have up to seven programmable output drive strengths. The user can select the drive strength of a particular output in the I/O Attribute Editor or can instantiate a specialized I/O macro, such as OUTBUF\_S\_12 (slew = low, out\_drive = 12 mA).

The maximum available drive strength is 24 mA per I/O. Though no I/O should be forced to source or sink more than 24 mA indefinitely, I/Os may handle a higher amount of current (refer to the device IBIS model for maximum source/sink current) during signal transition (AC current). Every device package has its own power dissipation limit; hence, power calculation must be performed accurately to determine how much current can be tolerated per I/O within that limit.

## I/O Interfacing

Low power flash devices are 5 V–input– and 5 V–output–tolerant if certain I/O standards are selected (refer to the "5 V Input and Output Tolerance" section on page 194). Along with other low-voltage I/O macros, this 5 V tolerance makes these devices suitable for many types of board component interfacing.

I/O Structures in IGLOOe and ProASIC3E Devices

# Low Power Flash Device I/O Support

The low power flash FPGAs listed in Table 8-1 support I/Os and the functions described in this document.

#### Table 8-1 • Flash-Based FPGAs

Series	Family <sup>*</sup>	Description
IGLOO	IGLOOe	Higher density IGLOO FPGAs with six PLLs and additional I/O standards
ProASIC3	ProASIC3E	Higher density ProASIC3 FPGAs with six PLLs and additional I/O standards
	ProASIC3L	ProASIC3 FPGAs supporting 1.2 V to 1.5 V with Flash*Freeze technology
	Military ProASIC3/EL	Military temperature A3PE600L, A3P1000, and A3PE3000L
	RT ProASIC3	Radiation-tolerant RT3PE600L and RT3PE3000L

Note: \*The device names link to the appropriate datasheet, including product brief, DC and switching characteristics, and packaging information.

### IGLOO Terminology

In documentation, the terms IGLOO series and IGLOO devices refer to all of the IGLOO devices as listed in Table 8-1. Where the information applies to only one product line or limited devices, these exclusions will be explicitly stated.

### ProASIC3 Terminology

In documentation, the terms ProASIC3 series and ProASIC3 devices refer to all of the ProASIC3 devices as listed in Table 8-1. Where the information applies to only one product line or limited devices, these exclusions will be explicitly stated.

To further understand the differences between the IGLOO and ProASIC3 devices, refer to the *Industry's Lowest Power FPGAs Portfolio.* 

This current draw can occur in the following cases:

- In Active and Static modes:
  - Input buffers with pull-up, driven Low
  - Input buffers with pull-down, driven High
  - Bidirectional buffers with pull-up, driven Low
  - Bidirectional buffers with pull-down, driven High
  - Output buffers with pull-up, driven Low
  - Output buffers with pull-down, driven High
  - Tristate buffers with pull-up, driven Low
  - Tristate buffers with pull-down, driven High
- In Flash\*Freeze mode:
  - Input buffers with pull-up, driven Low
  - Input buffers with pull-down, driven High
  - Bidirectional buffers with pull-up, driven Low
  - Bidirectional buffers with pull-down, driven High

## **Electrostatic Discharge Protection**

Low power flash devices are tested per JEDEC Standard JESD22-A114-B.

These devices contain clamp diodes at every I/O, global, and power pad. Clamp diodes protect all device pads against damage from ESD as well as from excessive voltage transients.

All IGLOO and ProASIC3 devices are tested to the Human Body Model (HBM) and the Charged Device Model (CDM).

Each I/O has two clamp diodes. One diode has its positive (P) side connected to the pad and its negative (N) side connected to VCCI. The second diode has its P side connected to GND and its N side connected to the pad. During operation, these diodes are normally biased in the off state, except when transient voltage is significantly above VCCI or below GND levels.

In 30 k gate devices, the first diode is always off. In other devices, the clamp diode is always on and cannot be switched off.

By selecting the appropriate I/O configuration, the diode is turned on or off. Refer to Table 8-13 for more information about the I/O standards and the clamp diode.

The second diode is always connected to the pad, regardless of the I/O configuration selected.

I/O Assignment	Clamp Diode	Hot Insertion	5 V Input Tolerance	Input Buffer	Output Buffer
3.3 V LVTTL/LVCMOS	No	Yes	Yes <sup>1</sup>	Enabled/Disabled	
3.3 V PCI, 3.3 V PCI-X	Yes	No	Yes <sup>1</sup>	Enabled/Disabled	
LVCMOS 2.5 V <sup>2</sup>	No	Yes	No	Enabled/Disabled	
LVCMOS 2.5 V / 5.0 V <sup>2</sup>	Yes	No	Yes <sup>3</sup>	Enabled/Disabled	
LVCMOS 1.8 V	No	Yes	No	Enabled/Disabled	
LVCMOS 1.5 V	No	Yes	No	Enabled/Disabled	
Voltage-Referenced Input Buffer		Yes	No	Enabled	/Disabled
Differential, LVDS/B-LVDS/M-LVDS/LVPECL	No	Yes	No	Enabled	/Disabled

#### Table 8-13 • I/O Hot-Swap and 5 V Input Tolerance Capabilities in IGLOOe and ProASIC3E Devices

Notes:

1. Can be implemented with an external IDT bus switch, resistor divider, or Zener with resistor.

- In the SmartGen Core Reference Guide, select the LVCMOS5 macro for the LVCMOS 2.5 V / 5.0 V I/O standard or the LVCMOS25 macro for the LVCMOS 2.5 V I/O standard.
- 3. Can be implemented with an external resistor and an internal clamp diode.

I/O Structures in IGLOOe and ProASIC3E Devices

## Conclusion

IGLOOe and ProASIC3E support for multiple I/O standards minimizes board-level components and makes possible a wide variety of applications. The Microsemi Designer software, integrated with Libero SoC, presents a clear visual display of I/O assignments, allowing users to verify I/O and board-level design requirements before programming the device. The IGLOOe and ProASIC3E device I/O features and functionalities ensure board designers can produce low-cost and low power FPGA applications fulfilling the complexities of contemporary design needs.

## **Related Documents**

## **Application Notes**

Board-Level Considerations http://www.microsemi.com/soc/documents/ALL\_AC276\_AN.pdf

## **User's Guides**

ProASIC3 FPGA Fabric User's Guide http://www.microsemi.com/soc/documents/PA3\_UG.pdf ProASIC3E FPGA Fabric User's Guide http://www.microsemi.com/soc/documents/PA3E\_UG.pdf IGLOOe FPGA Fabric User's Guide http://www.microsemi.com/soc/documents/IGLOOe\_UG.pdf Libero SoC User's Guide http://www.microsemi.com/soc/documents/libero\_ug.pdf IGLOO, Fusion, and ProASIC3 Macro Library Guide http://www.microsemi.com/soc/documents/pa3\_libguide\_ug.pdf SmartGen Core Reference Guide http://www.microsemi.com/soc/documents/genguide\_ug.pdf

## **Compiling the Design**

During Compile, a PDC I/O constraint file can be imported along with the netlist file. If only the netlist file is compiled, certain I/O assignments need to be completed before proceeding to Layout. All constraints that can be entered in PDC can also be entered using ChipPlanner, I/O Attribute Editor, and PinEditor.

There are certain rules that must be followed in implementing I/O register combining and the I/O DDR macro (refer to the I/O Registers section of the handbook for the device that you are using and the "DDR" section on page 256 for details). Provided these rules are met, the user can enable or disable I/O register combining by using the PDC command set\_io portname -register yes |no in the I/O Attribute Editor or selecting a check box in the Compile Options dialog box (see Figure 9-7). The Compile Options dialog box appears when the design is compiled for the first time. It can also be accessed by choosing **Options** > **Compile** during successive runs. I/O register combining is off by default. The PDC command overrides the setting in the Compile Options dialog box.

Figure 9-7 • Setting Register Combining During Compile

## Understanding the Compile Report

The I/O bank report is generated during Compile and displayed in the log window. This report lists the I/O assignments necessary before Layout can proceed.

When Designer is started, the I/O Bank Assigner tool is run automatically if the Layout command is executed. The I/O Bank Assigner takes care of the necessary I/O assignments. However, these assignments can also be made manually with MVN or by importing the PDC file. Refer to the "Assigning Technologies and VREF to I/O Banks" section on page 264 for further description.

The I/O bank report can also be extracted from Designer by choosing **Tools** > **Report** and setting the Report Type to **IOBank**.

This report has the following tables: I/O Function, I/O Technology, I/O Bank Resource Usage, and I/O Voltage Usage. This report is useful if the user wants to do I/O assignments manually.

UJTAG Applications in Microsemi's Low Power Flash Devices

# Conclusion

Microsemi low power flash FPGAs offer many unique advantages, such as security, nonvolatility, reprogrammablity, and low power—all in a single chip. In addition, Fusion, IGLOO, and ProASIC3 devices provide access to the JTAG port from core VersaTiles while the device is in normal operating mode. A wide range of available user-defined JTAG opcodes allows users to implement various types of applications, exploiting this feature of these devices. The connection between the JTAG port and core tiles is implemented through an embedded and hardwired UJTAG tile. A UJTAG tile can be instantiated in designs using the UJTAG library cell. This document presents multiple examples of UJTAG applications, such as dynamic reconfiguration, silicon test and debug, fine-tuning of the design, and RAM initialization. Each of these applications offers many useful advantages.

# **Related Documents**

## **Application Notes**

RAM Initialization and ROM Emulation in ProASIC<sup>PLUS</sup> Devices http://www.microsemi.com/soc/documents/APA RAM Initd AN.pdf

## **List of Changes**

The following table lists critical changes that were made in each revision of the chapter.

Date	Changes	Page		
December 2011	Information on the drive strength and slew rate of TDO pins was added to the "Silicon Testing and Debugging" section (SAR 31749).			
July 2010	This chapter is no longer published separately with its own part number and version but is now part of several FPGA fabric user's guides.			
v1.4 (December 2008)	IGLOO nano and ProASIC3 nano devices were added to Table 17-1 • Flash-Based FPGAs.	364		
v1.3 (October 2008)	The "UJTAG Support in Flash-Based Devices" section was revised to include new families and make the information more concise.			
	The title of Table 17-3 • Configuration Bits of Fusion, IGLOO, and ProASIC3 CCC Blocks was revised to include Fusion.	368		
v1.2 (June 2008)	The following changes were made to the family descriptions in Table 17-1 • Flash- Based FPGAs: • ProASIC3L was updated to include 1.5 V.	364		
	The number of PLLs for ProASIC3E was changed from five to six.			
v1.1 (March 2008)	The chapter was updated to include the IGLOO PLUS family and information regarding 15 k gate devices.	N/A		
	The "IGLOO Terminology" section and "ProASIC3 Terminology" section are new.	364		

Power-Up/-Down Behavior of Low Power Flash Devices

# Flash Devices Support Power-Up Behavior

The flash FPGAs listed in Table 18-1 support power-up behavior and the functions described in this document.

#### Table 18-1 • Flash-Based FPGAs

Series	Family <sup>*</sup>	Description
IGLOO	IGLOO	Ultra-low power 1.2 V to 1.5 V FPGAs with Flash*Freeze technology
	IGLOOe	Higher density IGLOO FPGAs with six PLLs and additional I/O standards
	IGLOO nano	The industry's lowest-power, smallest-size solution
	IGLOO PLUS	IGLOO FPGAs with enhanced I/O capabilities
ProASIC3	ProASIC3	Low power, high-performance 1.5 V FPGAs
	ProASIC3E	Higher density ProASIC3 FPGAs with six PLLs and additional I/O standards
	ProASIC3 nano	Lowest-cost solution with enhanced I/O capabilities
	ProASIC3L	ProASIC3 FPGAs supporting 1.2 V to 1.5 V with Flash*Freeze technology
	RT ProASIC3	Radiation-tolerant RT3PE600L and RT3PE3000L
	Military ProASIC3/EL	Military temperature A3PE600L, A3P1000, and A3PE3000L
	Automotive ProASIC3	ProASIC3 FPGAs qualified for automotive applications

Note: \*The device names link to the appropriate datasheet, including product brief, DC and switching characteristics, and packaging information.

### IGLOO Terminology

In documentation, the terms IGLOO series and IGLOO devices refer to all of the IGLOO devices as listed in Table 18-1. Where the information applies to only one product line or limited devices, these exclusions will be explicitly stated.

### ProASIC3 Terminology

In documentation, the terms ProASIC3 series and ProASIC3 devices refer to all of the ProASIC3 devices as listed in Table 18-1. Where the information applies to only one product line or limited devices, these exclusions will be explicitly stated.

To further understand the differences between the IGLOO and ProASIC3 devices, refer to the *Industry's Lowest Power FPGAs Portfolio*.



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